

PNP HIGH POWER SILICON TRANSISTOR

Qualified per MIL-PRF-19500/ 461

Devices

2N6211

2N6212

2N6213

Qualified Level

JAN
JANTX
JANTXV

MAXIMUM RATINGS

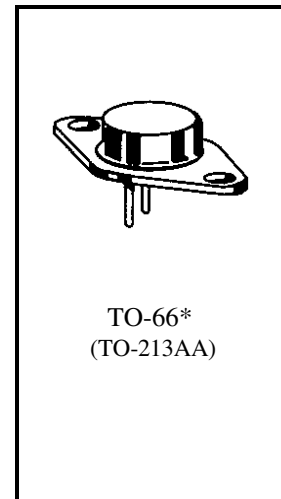
Ratings	Symbol	2N6211	2N6212	2N6213	Unit
Collector-Emitter Voltage	V_{CEO}	225	300	350	Vdc
Collector-Base Voltage	V_{CBO}	275	350	400	Vdc
Emitter-Base Voltage	V_{EBO}	6.0			Vdc
Base Current	I_B	1.0			Adc
Collector Current	I_C	2.0			Adc
Total Power Dissipation	P_T	@ $T_A = +25^{\circ}C$ ⁽¹⁾	3.0		W
		@ $T_C = +25^{\circ}C$ ⁽²⁾	35		W
Operating & Storage Temperature	T_{op}, T_{stg}	-55 to +200			$^{\circ}C$

THERMAL CHARACTERISTICS

Characteristics	Symbol	Max.	Unit
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	5.0	$^{\circ}C/W$

1) Derate linearly 17.1 mW/ $^{\circ}C$ for $T_A > +25^{\circ}C$

2) Derate linearly 200 mW/ $^{\circ}C$ for $T_C > +25^{\circ}C$



*See appendix A for package outline

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

Characteristics	Symbol	Min.	Max.	Unit
-----------------	--------	------	------	------

OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage $I_C = 200$ mAdc, $f = 30$ -60 Hz	2N6211 2N6212 2N6213	$V_{(BR)CEO}$	225 300 350	Vdc
Collector-Emitter Breakdown Voltage $I_C = 200$ mAdc, $f = 30$ -60 Hz, $R_{BE} = 50 \Omega$	2N6211 2N6212 2N6213	$V_{(BR)CER}$	250 325 375	Vdc
Collector-Emitter Breakdown Voltage $I_C = 200$ mAdc, $f = 30$ -60 Hz, $R_{BE} = 50 \Omega$, $V_{BE} = -1.5$ Vdc	2N6211 2N6212 2N6213	$V_{(BR)CEX}$	275 350 400	Vdc

